

Perpendicular magnetic anisotropy in $\text{Mn}_{2-\delta}\text{CoGa}_{1+\delta}$ films

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Half metals which have perfect spin-polarization of electrons at the Fermi level is one of the promising materials for improving spintronics devices. Mn_2CoGa is an inverse Heusler alloy showing half-metallic electronic structure[1]. One of interesting physical properties for Mn_2CoGa is a relatively high resistivity[2] compared with those of Co-based half-metallic full Heusler alloys which have been applied for current perpendicular to plane giant magnetoresistance (CPP-GMR) devices to date[3].

It was also reported that magnetic anisotropy of Mn_2CoGa films depended on the buffer layer material[2]. Although the control of anisotropy is important for half-metallic materials, the key factor for manipulating the anisotropy is still unclear. In this work, we have investigated the relationship between crystal structure and magnetic anisotropy of Mn_2CoGa films with several buffer layer materials and the layer thicknesses.

The samples were deposited onto single crystal $\text{MgO}(100)$ substrates by using an ultrahigh vacuum magnetron sputtering machine. We adopted two materials for the buffer layer; Cr or Ag. The stacking structures are as follows:

Cr buffer samples: $\text{MgO sub.} / \text{Cr (20 nm)} / \text{Mn-Co-Ga (} t \text{)} / \text{Ta (3 nm)}$

Ag buffer samples: $\text{MgO sub.} / \text{Cr (20 nm)} / \text{Ag (40 nm)} / \text{Mn-Co-Ga (} t \text{)} / \text{Ta (3 nm)}$

The stoichiometric ratio is $\text{Mn}_{1.7}\text{Co}_{1.0}\text{Ga}_{1.3}$ for the Mn-Co-Ga layer. Mn-Co-Ga thicknesses (t) are 5 nm, 10 nm, 20 nm and 30 nm.

Crystal structures and magnetic properties were investigated by using x-ray diffractometer (XRD) and vibrating sample magnetometer (VSM), respectively.

Perpendicular magnetized Mn-Co-Ga films were achieved for the Cr buffer samples, but on the other hand, those onto Ag buffer showed in-plane magnetization.

The in-plane and out-of-plane lattice constants, a and c , were evaluated from diffraction peaks by XRD measurements. The c/a ratio was greater than 1 for the Cr buffer samples, and that was nearly 1 for the Ag buffer samples. The XRD results suggest that the perpendicular magnetization of the Mn-Co-Ga on Cr buffer originates from the tetragonal strain.

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References

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